and wherein

59. The method of fabricating a semiconductor device in accordance with 44,

wherein said laser annealing is performed by applying a laser beam in the form of

sheet.

REMARKS

Claims 44-59 are pending in this application. The claims represent claims 45, 46, 48-56, 60 and 73-76 which were cancelled in the parent application. No new matter is contained in the amendments.

Please charge any fee deficiency or credit any overpayment to Deposit Account No. 01-2300.

Respectfully submitted,

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